

Claims

- [c1] 1.A method of defect review comprising following steps:
providing a wafer with a plurality of defects;
performing a defect inspection to detect the defects;
performing an automatic defect classification according
to a database to separate the defects into a plurality of
defect types; and
performing a defect review;
wherein each defect type has different sampling ratios in
the defect review according to its influence degree of
process yield.
- [c2] 2.The method of claim 1 wherein the database comprises
information about the plurality of defect types and defect
information corresponding to each defect type.
- [c3] 3.The method of claim 2 wherein the defect information
comprises the influence degree of the process yield of
each defect type.
- [c4] 4.The method of claim 3 wherein the database separates
the defect types into killer defects and non-killer defects
according to the influence degree of the process yield.

- [c5] 5.The method of claim 4 wherein the sampling ratio of the killer defects in the defect review is larger than that of the non-killer defects.
- [c6] 6.The method of claim 3 wherein the database separates the defects into pre-layer defects and adding defects, and further separates the adding defects into killer defects and non-killer defects.
- [c7] 7.The method of claim 6 wherein the defect review focuses on the adding defects.
- [c8] 8.The method of claim 1 wherein after finishing the defect inspection, a judgment of cluster defects is performed and a defect review with a high sampling ratio is performed on the cluster defects if the cluster defects exist.
- [c9] 9.The method of claim 1 wherein the database is updated according to the result of the defect review after finishing the defect review.